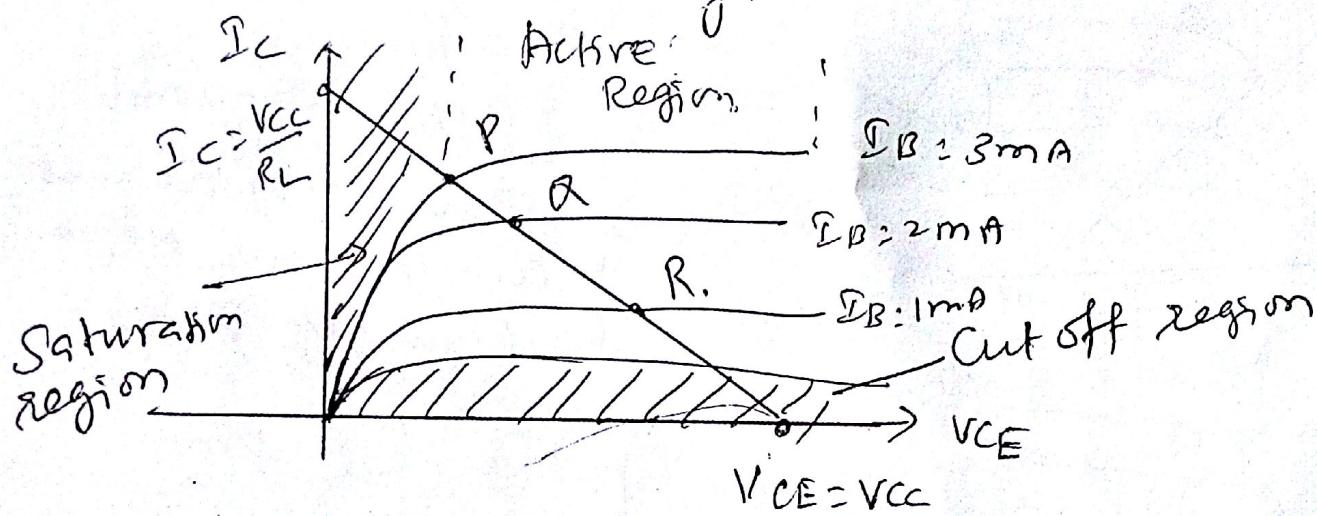


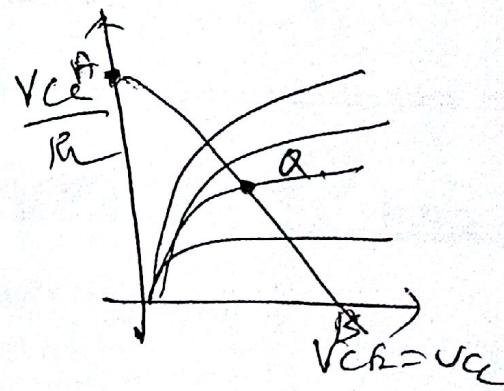
## Need for Biasing

To fix the Q-point in the middle of active region, we go for biasing. The proper flow of zero signal collector current and maintenance of proper collector emitter voltage during the passage of signal is known as transistor biasing.



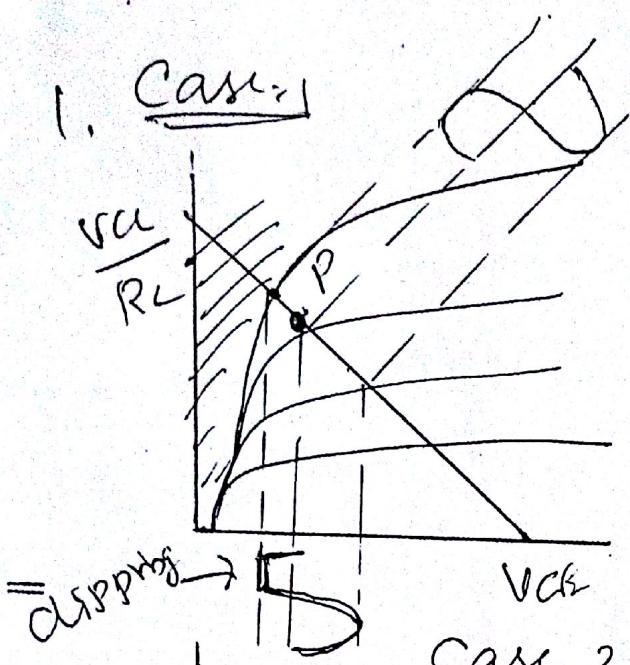
## Q-point or operating point or Quiescent point

- \* The zero signal values of  $I_C$  &  $V_{CE}$  are known as operating point.
- \* These two zero signal values are noted as 'A' & 'B'.
- \* The line drawn between A and B is called DC load line.
- \* The intercept point with DC load line is called Q-point.



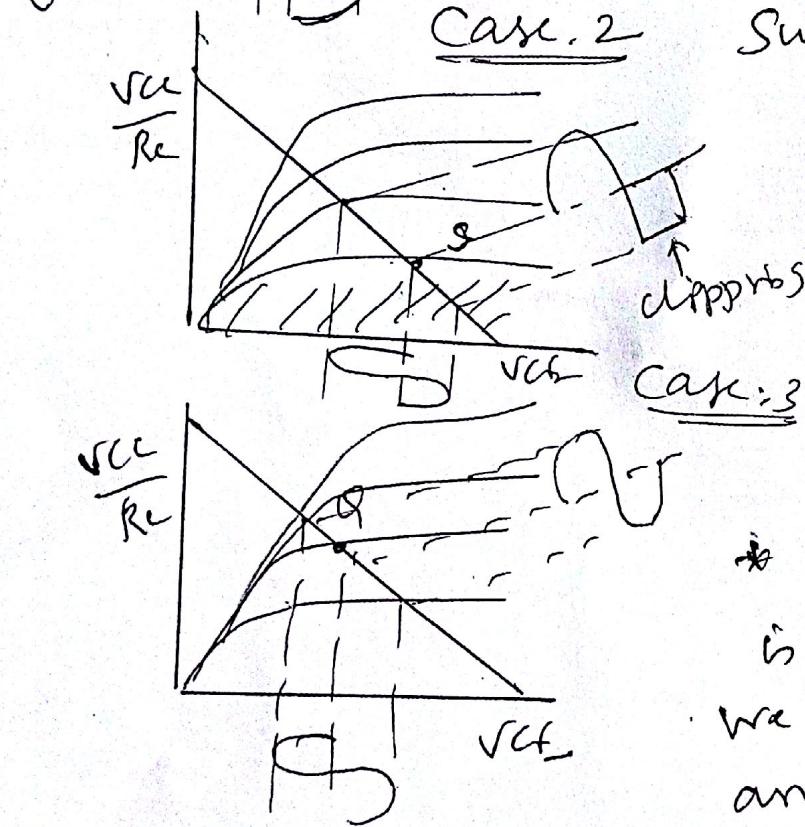
# Selection of Q-point.

## 1. Case-1



- \* If the Q-point is placed at point 'P' very nearer to saturation
- \* Collector current clipping at the positive half-cycle
- \* ∵ point 'P' is not suitable for operating point

## Case. 2



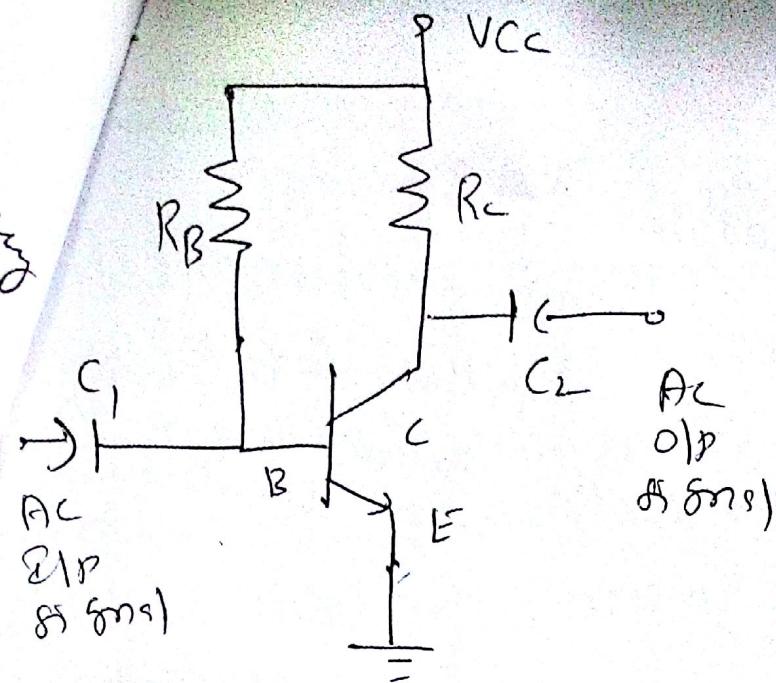
- \* If the Q-point is placed (S) nearest to cut-off region, negative half-cycle get clipped.
- \* If the Q-point is fixed at point 'Q', we get the D.C without any distortion.

## fixed Bias circuit.

It is the simplest DC Bias Configuration Compensator

DC Analysis.

Reactance of the capacitor  $X_C = \frac{1}{2\pi f C}$



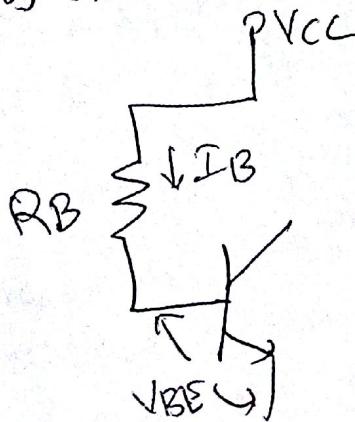
Fig(1) Fixed Bias Circuit

for  $\omega C = f = 0$

$$X_C = \frac{1}{\omega} = \infty$$

We can replace capacitor with an open circuit because the reactance of the capacitor is  $\infty$ .

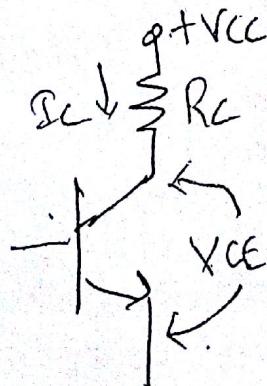
Bias circuit:



$$V_{CC} = I_B R_B + V_{BE}$$

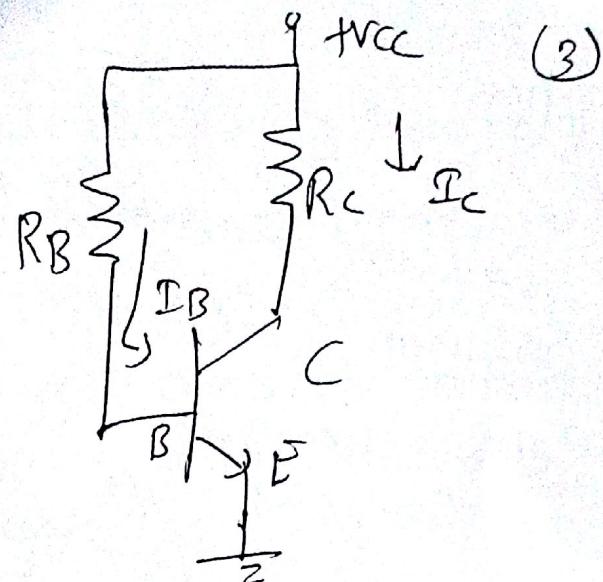
$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$

Collector Circuit:



$$V_{CC} = I_C R_C + V_{CE}$$

$$I_C = \frac{V_{CC} - V_{CE}}{R_C}$$



Fig(2) AC equivalent circuit

WICR  $I_E = \beta I_B$   
 Collector current ( $I_C$ ) is related to  $I_B$  by  $I_C = \frac{I_E}{\beta}$ .  
 Constant of  $\beta$ ,  $I_C$  is not a function of  $R_C$ .  $I_C$  will not affect  $I_C \propto I_B$ .  
 as long as we remain in the active region of the device.

$$V_{CE} = V_C - V_E$$

$$V_{BE} = V_B - V_E$$

## Variation of Q-point. (Quiescent point)

Biasing Circuit should be designed to fix the Q-point at the centre of the active region. Designing the circuit to stabilize the Q-point is known as bias stability.  
 Following factors affecting the Q-point

(1) Temperature

$\leq$   
 $I_{CO}$   
 $V_{BE}$   
 $\beta_{dc}$

(2) Variation of life ( $T_S$ )

### Temperature

The change in temp affect the following parameters of the transistor-

1.  $I_{CO}$  (Leakage Current)

2.  $V_{BE}$

3.  $\beta_{dc}$

### $I_{CO}$ :

The flow of current in the circuit produces heat at the junctions. This heat increases the temperature at the junctions. Minority carriers are temperature dependent  $\rightarrow$  minority carrier increase due to temperature increment. The increase in the minority carriers increases the leakage current  $I_{CO}$ .

$$I_{CEO} = (1 + \beta) I_{CBO}$$

$I_{CBO}$  doubles for every  $10^\circ C$  rise in temperature. Increase in  $I_{CBO}$  return increases the collector current.

$$I_C = \beta I_B + I_{CEO}$$

Excessive increase in  $I_C$  shift the operating point into saturation region.

The increase in collector current ( $I_C$ ) increases the power dissipation at the collector junction. This in turn further increases the temperature. Hence increases the collector current. The excess heat produced at cumulative. The excess heat may burn the collector base junction and destroy the transistor. This situation is called Thermal Runaway of the transistor.

## $V_{BE}$ : (Base to Emitter voltage)

$V_{BE}$  changes with temp at the rate of  $2.5 \text{ mV}^{\circ}\text{C}^{-1}$ .  
 Base current  $I_B$  depends upon  $V_{BE}$ ,  $T_C$ .  
 depends upon  $I_B$ .  $\therefore I_C$  changes with  $I_B$  due to temperature.

$\beta_{dc}$ :  $\beta_{dc}$  of the transistor is also temperature dependent. As  $\beta_{dc}$  varies  $I_C$  also varies. The change in collector current change the operating point.

## Variation of $h_{fe}(\beta)$

No two transistors have the same characteristics. There is a change in the  $\beta$  value in practice. The biasing circuit is designed according to the ' $\beta$ ' value. Due to change in ' $\beta$ ', the operating point may shift.

## Requirements of a Biasing Circuit

To maintain the operating point stable by keeping  $I_C$  &  $V_{CE}$  constant so that the transistor will always work in active region. The following techniques are normally used.

- ① Stabilization Techniques.
- ② Compensation Techniques.

## Stabilization Technique.

(3)

It refers to the use of resistive biasing circuits which allow  $I_B$  to vary so as to keep  $I_C$  relatively constant with variations in  $I_{CO}$ ,  $\beta$  &  $V_{BE}$ .

## Compensation Techniques.

It refers to the use of temperature.

Sensitive devices such as diodes, transistors, thermistors etc. which provides compensating voltage and current to maintain the operating point.

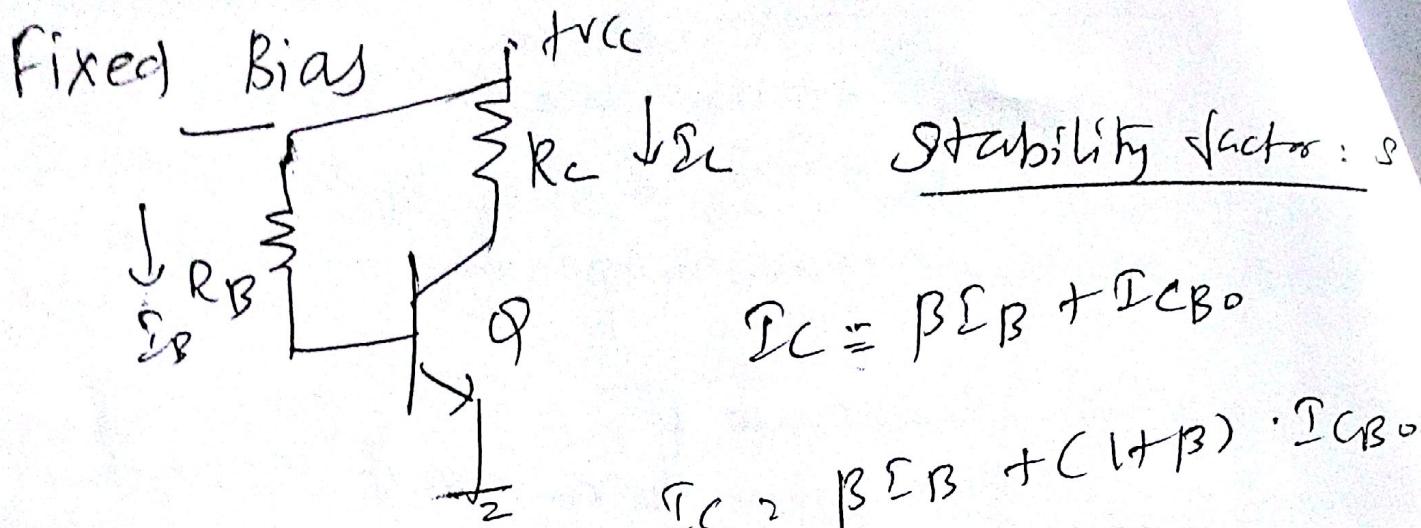
## Stability factor.

Degree of change in operating point due to variation in temperature is called stability factor.

$$1) S = \left| \frac{\partial I_C}{\partial I_{CO}} \right|_{V_{BE}, \beta}$$

$$2) S' = \left| \frac{\partial I_C}{\partial V_{BE}} \right|_{I_{CO}, \beta}$$

$$3) S'' = \left| \frac{\partial I_C}{\partial \beta} \right|_{I_{CO}, V_{BE}}$$



$$I_C = \beta I_B + I_{CB0}$$

$$I_C = \beta I_B + (1+\beta) \cdot I_{CB0}$$

$$\frac{\partial I_C}{\partial I_B} = \beta + (1+\beta) \cdot \frac{\partial I_{CB0}}{\partial I_C}$$

$$1 = \beta \cdot \frac{\partial I_B}{\partial I_C} + (1+\beta) \cdot \frac{\partial I_{CB0}}{\partial I_C}$$

$$\frac{\partial I_{CB0}}{\partial I_C} = -\frac{\beta \frac{\partial I_B}{\partial I_C}}{1+\beta}$$

$$\therefore \cancel{\phi} = \cancel{\beta} \cdot S = \frac{\partial I_C}{\partial I_{CB0}}$$

$$\boxed{S = \frac{1+\beta}{1-\beta \cdot \frac{\partial I_B}{\partial I_C}}}$$

(For the fixed bias  $V_{BE} \rightarrow \beta$  are constant)

$$I_B = \frac{V_{CC} - V_{BE}}{R_B} \approx \frac{V_{CC}}{R_B} \quad \left[ V_{BE} \xrightarrow{\text{small}} \right]$$

$$\frac{\partial I_B}{\partial R_C} = 0$$

$$S = \frac{\frac{\partial I}{\partial \alpha} (1+\beta)}{1-\alpha} = 1+\beta \quad (9)$$

$$\boxed{S = 1+\beta}$$

Stability factor  $s'$

$$S' = \frac{\frac{\partial I_C}{\partial V_{BE}}}{I_{C0}, \beta} \quad |$$

WICR

$$I_C = \beta I_B + (1+\beta) \cdot I_{CB0}$$

$$I_C = \beta \left( \frac{V_{CC} - V_{BE}}{R_B} \right) + (1+\beta) \cdot I_{CB0}$$

$$\begin{aligned} \frac{\partial I_C}{\partial V_{BE}} &= \beta \frac{-V_{CC}}{R_B} - \beta \frac{V_{BE}}{R_B} + (1+\beta) \cdot I_{CB0} \\ &= 0 - \beta \frac{1}{R_B} + 0 = -\beta \frac{1}{R_B} \end{aligned}$$

$$\boxed{S' = -\beta / R_B}$$

Stability factor  $S''$  Relation between  $S$  &  $S'$

$$\text{WICR} \quad S = 1+\beta; \quad S' = -\beta / R_B$$

Multiply Nr 6 or by  $(1+\beta)$

$$S' = \frac{-\beta(1+\beta)}{R_B(1+\beta)}$$

$$S' = \frac{-\beta S}{R_B(1+\beta)}$$

Stability factor  $S''$

$$S'' = \left. \frac{\partial I_C}{\partial \beta} \right|_{V_{BE}, I_{CO}}$$

$$I_C = \frac{\beta V_{CC}}{R_B} - \frac{\beta V_{BE}}{R_B} + (1+\beta) I_{CB0}$$

$$\frac{\partial I_C}{\partial \beta} = \frac{V_{CC}}{R_B} - \frac{V_{BE}}{R_B} + 1 + \beta I_{CB0}$$

$$\frac{\partial I_C}{\partial \beta} = I_B + I_{CB0} = \frac{I_C}{\beta}$$

$$\frac{\partial I_C}{\partial \beta} = I_B / \beta \quad \text{since } I_B = I_C / \beta \quad \text{so } I_B \gg I_{CB0}$$

Relation between  $S$  &  $S''$

$$S = 1 + \beta; \quad S'' = I_C / \beta.$$

$$S'' = \frac{I_C(1+\beta)}{\beta(1+\beta)}$$

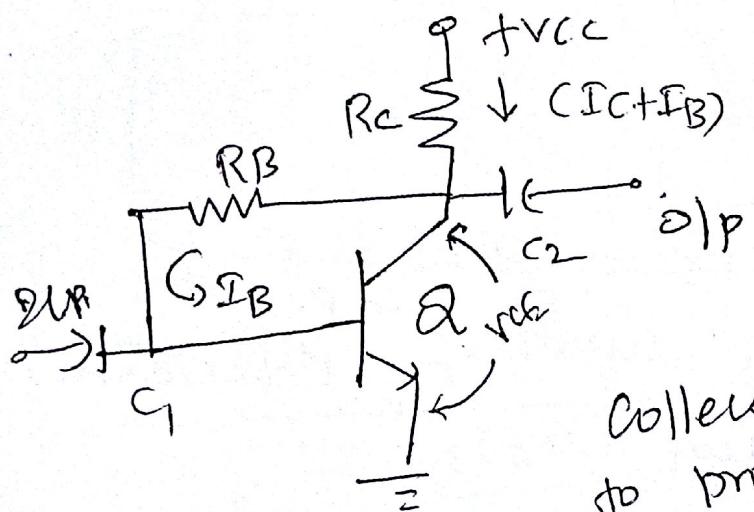
$$S'' = \frac{I_C \cdot S}{\beta(1+\beta)}$$

# Various Biasing Methods

(11)

1. Fixed Bias
2. Collector to Base Bias
3. Voltage Divider / Self Bias Circuit
4. Emitter Stabilized Bias Circuit
5. Miscellaneous Bias Circuit

## Collector to Base Bias Circuit



It is an improvement over fixed bias circuit. Here biasing resistor is connected between the collector and base of the transistor to provide a feedback path through  $R_B$  so  $(I_C + I_B)$  flows

Thus  $I_B$  flows through  $R_E$

## Circuit Analysis

### Base circuit

$$V_{CC} = (I_C + I_B) \cdot R_E + I_B R_B + V_{BE}$$

$$V_{CC} = I_C R_E + I_B R_E + I_B R_B + V_{BE}$$

$$V_{CC} = I_B (R_E + R_B) + V_{BE}$$

$$I_B (R_E + R_B) = V_{CC} - V_{BE}$$

$$V_{CC} = (R_B + R_C) \cdot I_B + \beta I_B \cdot R_C + V_{BE}$$

$$V_{CC} = R_B I_B + \underline{R_C I_B} + \beta \underline{I_B R_C} + V_{BE}$$

$$V_{CC} = I_B [ (1 + \beta) R_C + R_B ] + V_{BE}$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (1 + \beta) \cdot R_C}$$

$\therefore \beta \gg 1$

$$\boxed{I_B = \frac{V_{CC} - V_{BE}}{R_B + \beta R_C}}$$

### Collector circuit:

$$V_{CC} = (I_C + I_B) R_C + V_{CE}$$

Collector current  $I_C$  changes due to temp. If  $R_C$  increases, voltage drop across  $R_C$  increases.

$$V_{CE} = V_{CC} - (I_C + I_B) R_C$$

But  $V_{CC}$  is constant, so  $V_{CE}$  get reduced.  
 Due to reduction in  $V_{CE}$   $I_B$  reduces. As  $I_C$  depends on  $I_B$ ,  $I_C$  also reduces. In this way this circuit maintains stability.

$$0 : \frac{\partial I_C}{\partial R_C} + \beta \frac{\partial I_B}{\partial R_B} (R_B + R_C) \quad (1)$$

$$\frac{\partial I_B}{\partial R_B} (R_B + R_C) = - \frac{\partial I_C}{\partial R_C}$$

$$\frac{\partial I_B}{\partial R_C} = \frac{-R_C}{R_B + R_C}$$

WKR

$$S_2 = \frac{1 + \beta}{1 + \beta \left( \frac{\partial I_B}{\partial I_C} \right)}$$

$$S = \frac{1 + \beta}{1 + \beta \left( \frac{R_C}{R_B + R_C} \right)}$$

If has lesser stability factor than fixed bias

stability factor S'

$$\frac{\partial I_C}{\partial V_{BE}} = ? \quad (I_C + I_B) R_C + I_B R_B + V_{BE}$$

$$V_{CC} = (R_B + R_C) I_B + I_C R_C + V_{BE}$$

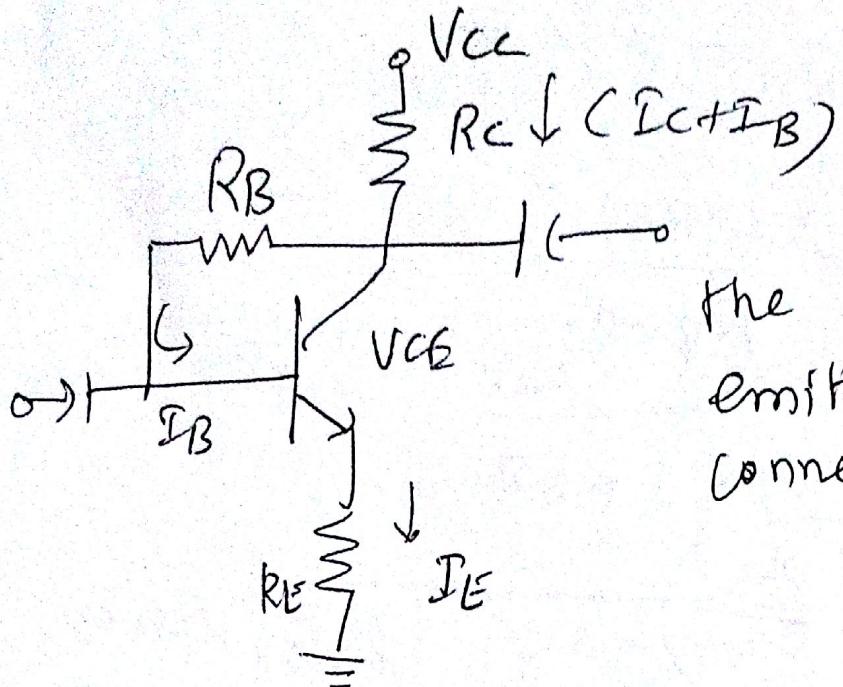
$$I_B = \frac{V_{CC} - V_{BE} - I_C R_C}{R_C + R_B}$$

$$\left[ \frac{I_C}{\beta} = I_B \right]$$

$$\frac{I_C}{\beta} + \frac{I_C R_C}{R_C + R_B} = \frac{V_{CC} - V_{BE}}{R_C + R_B}$$

$$I_C \left[ \frac{1}{\beta} + \frac{R_C}{R_C + R_B} \right] = \frac{V_{CC} - V_{BE}}{R_C + R_B}$$

# Modified Collelter To Base Bias Circuit



\* To further improve the level of stability, the emitter resistance is connected in this circuit.

## Base circuit:

$$V_{CC} = (I_C + I_B) R_C + R_B I_B + V_{BE} + I_E R_E$$

$$(R_C + R_B) I_B = V_{CC} - V_{BE} - I_E R_E - I_C R_C$$

$$I_B = \frac{V_{CC} - V_{BE} - I_E R_E - I_C R_C}{R_C + R_B}$$

## Collector Current:

$$V_{CC} = (I_C + I_B) R_C + V_{CE} + I_E R_E$$

$$I_C R_C = \frac{V_{CC} - V_{CE} - I_E R_E - I_B R_C}{R_C}$$

## Stability factor (S)

$$V_{CC} = I_C R_C + I_B (R_C + R_B) + V_{BE}$$

$V_{CC}$  &  $V_{BE}$  are constant.

$$I_C \left[ \frac{R_C + R_B + R_{C\beta}}{\beta(R_C + R_B)} \right] = \frac{V_{CC} - V_{BE}}{R_C + R_B} \quad (15)$$

$$I_C = \frac{(V_{CC} - V_{BE}) \cdot \beta(R_C + R_B)}{(R_C + R_B) (R_C + R_B + \beta R_C)}$$

$$I_C = \frac{\beta (V_{CC} - V_{BE})}{R_B + R_C (1 + \beta)}$$

$$\frac{\partial I_C}{\partial V_{BE}} = \frac{-\beta}{R_B + (1 + \beta) R_C}$$

$$S''_2 = \frac{-\beta}{R_B + (1 + \beta) R_C}$$

Stability factor  $S''$

$$S''_2 = \frac{\partial I_C}{\partial \beta}$$

$$\left[ \frac{d}{dt} \left( \frac{u}{v} \right) \right] = \frac{\frac{du}{dt} - \frac{u}{v^2} \frac{dv}{dt}}{v^2}$$

$$I_C = \frac{\beta (V_{CC} - V_{BE})}{R_B + (1 + \beta) R_C}$$

$$\frac{\partial I_C}{\partial \beta} = \frac{[(1 + \beta) R_C + R_B] [V_{CC} - V_{BE}]}{(1 + \beta) R_C + R_B)^2} - \beta (V_{CC} - V_{BE}) R_C$$

$$\begin{aligned}
 &= \frac{V_{CC} - V_{BE}}{\left[ (1+\beta) R_C + R_B \right]^2} \left[ (1+\beta) \cdot R_C + R_B - \beta R_C \right] \\
 &= \frac{(V_{CC} - V_{BE}) (R_C + R_B)}{\left[ (1+\beta) R_C + R_B \right]^2} \\
 &= \frac{(V_{CC} - V_{BE}) (R_C + R_B)}{\left[ (1+\beta) R_C + R_B \right] \left[ (1+\beta) R_C + R_B \right]}
 \end{aligned}$$

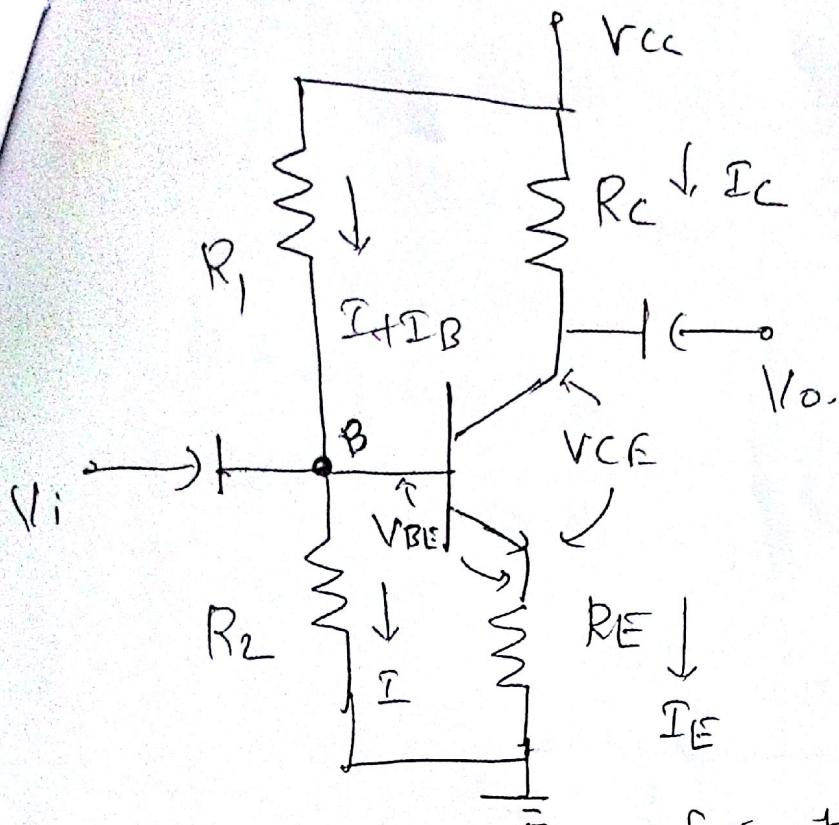
$S'':$

$$V_{DS} = \frac{I_C (R_D + R_C)}{\beta \left[ (1+\beta) R_C + R_B \right]}$$

$$S''' = \left[ I_C = \frac{\beta (V_{CC} - V_{BE})}{(1+\beta) R_C + R_B} \right]$$

### Voltage Divider Bias [self bias]

Biasing is provided by three resistances  $R_1 + R_2 + R_E$ .  $R_1 + R_2$  act as a potential divider, giving a fixed voltage to point B. If 'I<sub>C</sub>' current increases due to temperature, the emitter current 'I<sub>E</sub>' also increases. and the voltage drop across  $R_E$  increases.

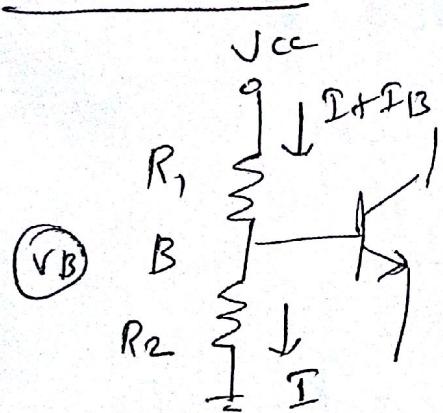


It reduces the (17)  
Voltage drop  
between base &  
emitter, ( $V_{BE}$ ).  
Due to reduction  
in  $V_{BE}$ ,  $I_B$   
reduces. Due to  $I_B$   
reduces,  $I_C$  gets reduced.  
This reduction in  
 $I_C$  compensates  
original change in  $I_C$ .  
for the original change in  $I_C$ .

Negative feedback exists in this circuit.

### Circuit Analysis

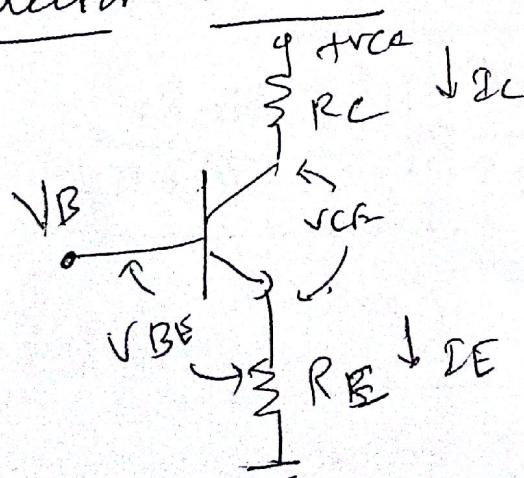
#### Base Circuit



$$V_B = \frac{R_L}{R_1 + R_2} \times V_{CC}$$

$$V_E = I_E R_E = V_B - V_{BE}$$

#### Collector Circuit

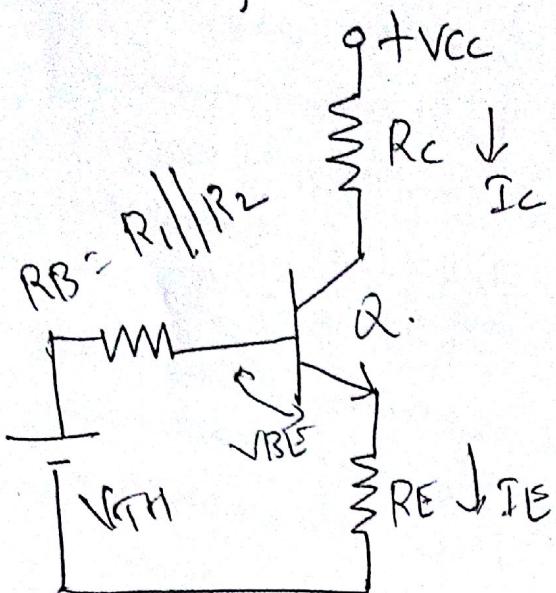


$$I_E = \frac{V_B - V_{BE}}{R_E}$$

apply KVL  
 $V_{CC} = I_C R_C + V_{CE} + I_E R_E$

$$V_{CE} = V_{CC} - I_C R_C - I_E R_E$$

## Simplified Circuit of Voltage Divider Bias



$R_1$  and  $R_2$  replaced by  $R_B$ ,  
 $V_{TH}$ .

$R_B \rightarrow$  parallel combination of  $R_1 \parallel R_2$   
 $V_{TH} \rightarrow$  Thevenin's Voltage.

$$R_B = \frac{R_1 R_2}{R_1 + R_2}$$

Apply KVL to the base circuit.

$$V_{TH} = I_B R_B + V_{BE} + I_E R_E \quad [I_E = I_C + I_B]$$

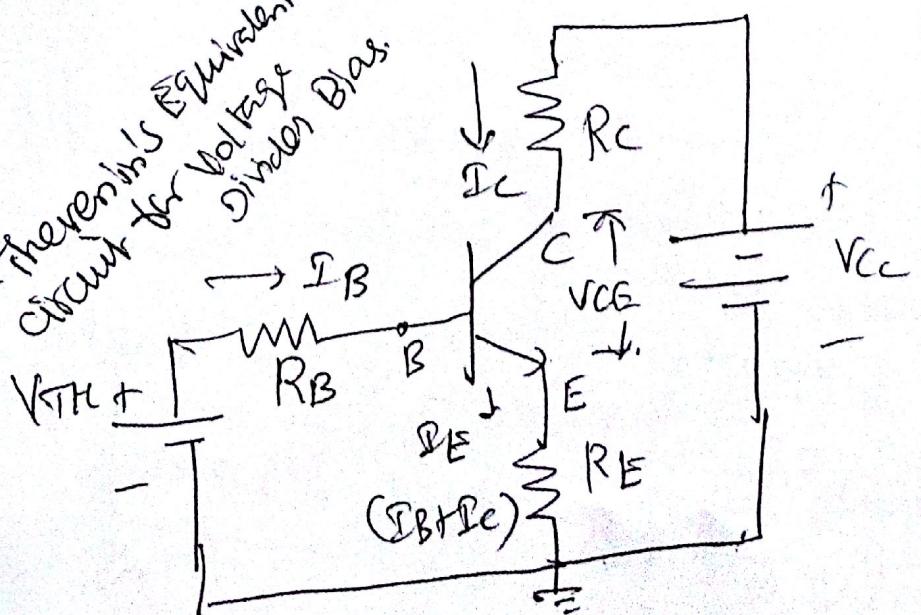
$$V_{TH} = I_B R_B + I_C R_E + I_B R_E + V_{BE}$$

$$V_{TH} = I_B (R_B + R_E) + I_C R_E + V_{BE}$$

$$V_{BE} = V_{TH} - (R_B + R_E) I_B - I_C R_E$$

## Stability factor (s)

Thevenin's Equivalent  
Voltage Divider Bias



$$V_{TH} = \frac{R_2}{R_1 + R_2} \cdot V_{CC}$$

$$R_B = \frac{R_2 R_1}{R_1 + R_2}$$

Apply KVL to the Base circuit;

$$V_{TH} = I_B R_B + V_{BE} + (I_B + I_C) \cdot R_E$$

diff w.r.t  $I_C$

$$0 = \frac{\partial I_B}{\partial I_C} R_B + 0 + \frac{\partial I_B}{\partial I_C} \cdot R_E + R_E$$

$$\frac{\partial I_B}{\partial I_C} (R_B + R_E) = -R_E$$

$$\boxed{\frac{\partial I_B}{\partial I_C} = \frac{-R_E}{R_B + R_E}}$$

1) ready w.l.o.g

$$S = \frac{1+\beta}{1 + \beta \left( \frac{\partial I_B}{\partial I_C} \right)}$$

$$S = \frac{1+\beta}{1 + \beta \left( \frac{-R_E}{R_B + R_E} \right)}$$

$$\boxed{S = \frac{1+\beta}{1 + \beta \frac{R_E}{R_B + R_E}}}$$

$$S = \frac{(1+\beta)(R_B + R_E)}{R_B + R_E + \beta R_E}$$

$$S = \frac{(1+\beta)(R_B + R_E)}{R_B + (1+\beta)R_E}$$

$\therefore$  Each term by  $R_E$

$$S = \frac{(1+\beta)(1 + R_B/R_E)}{(1+\beta) + R_B/R_E}$$

From eqn, we can observe the following  
 ①  $R_B/R_E$  Controls the value of stability factor's.

If  $R_B/R_E \ll 1$ , then.

$$S = \frac{(1+\beta)}{1+\beta} = 1$$

Practically,  $R_B/R_E \neq 0$ , But we can maintain  $R_B/R_E$  as small as possible

② To keep  $R_B/R_E$  small, it is necessary to keep  $R_B$  small. This means that  $R_1 \parallel R_2$  must be small. Due to small value of  $R_1 \parallel R_2$  it will reduce the current drawn from Vcc while designing.  $R_f$  must be smaller than  $R_2$ .

③ By increasing  $R_E$ , we can improve 'S'. But if  $R_E$  increases drop

across  $R_E$  increases. Since  $V_{CC}$  is constant, (21)  
 drop across  $R_E$  will reduce. It will  
 shift the Q point. Hence there is a  
 limit in increasing  $R_E$ .

$s \rightarrow$  Small

$R_B$  - Reasonably small.

$R_E$  = Not very large,

i.e. If  $R_B/R_E$  is fixed;  $\beta$  affect the 's' value

Stability factor 's'

$$s' = \frac{\partial I_C}{\partial V_{BE}} \Big|_{I_{CO}, \beta}$$

$$I_C = (1 + \beta) I_{CO} + \beta I_B$$

$$V_{TH} = \Sigma B R_B + V_{BIE} + (I_B + I_C) R_E$$

$$V_{BIE} = V_{TH} - (R_E + R_B) I_B - R_E I_C$$

$$I_B = \frac{I_C - (1 + \beta) \cdot I_{CO}}{\beta}$$

$$\text{Sub } \Sigma B \text{ vs } V_{BIE} \text{ eqn.}$$

$$V_{BIE} = V_{TH} - (R_E + R_B) \left[ \frac{I_C - (1 + \beta) I_{CO}}{\beta} \right] - R_E$$

$$V_{BE} = V_{TH} - \frac{(R_E + R_B) \cdot I_C}{\beta} + \frac{(R_E + R_B)(1 + \beta)I_{CO}}{\beta}$$

$$V_{BE} = V_{TH} - \left[ \frac{(1 + \beta) R_E + R_B}{\beta} I_C \right] + \frac{(R_E + R_B)(1 + \beta) I_{CO}}{\beta}$$

Diff w.r.t  $V_{BE}$  w.r.t  $I_C$

$$1' = 0 - \frac{[R_B + (1 + \beta) R_E]}{\beta} \frac{\partial I_C}{\partial V_{BE}} + 0$$

$$\therefore \frac{\partial I_C}{\partial V_{BE}} = \frac{-\beta}{R_B + (1 + \beta) R_E}$$

$$S' = \frac{-\beta}{R_B + (1 + \beta) R_E}$$

Stability factor  $S''$

$$S'' = \frac{\partial I_C}{\partial \beta} \quad / \quad V_{BE}, I_{CO}$$

$$V_{BE} = V_{TH} - \frac{R_B + (1 + \beta) R_E}{\beta} \cdot I_C + \frac{(R_E + R_B)(1 + \beta)}{\beta}$$

$$= V_{TH} - \frac{R_B + (1 + \beta) R_E}{\beta} I_C + V'$$

$$\text{where } V' = \left[ \frac{(R_B + R_E)(1+\beta)}{\beta} \right] I_{Co.}$$

$$= (R_B + R_E) I_{Co.} \quad \because \beta \gg 1$$

$$I_C = \frac{\beta [V_{TH} + V' - V_{BE}]}{R_B + R_E(1+\beta)}$$

Diff. So take  $V'$  independent of  $\beta$ , then

$$\frac{\partial I_C}{\partial \beta} = \frac{R_B + R_E(1+\beta) (V_{TH} + V' - V_{BE}) - \beta (V_{TH} + V' - V_{BE})}{[R_B + R_E(1+\beta)]^2}$$

Multiply NR & DR by  $(1+\beta)$

$$\frac{\partial I_C}{\partial \beta} = \frac{(1+\beta)(R_B + R_E)}{(1+\beta)[R_B + R_E(1+\beta)]} \frac{(V_{TH} + V' - V_{BE})}{[R_B + R_E(1+\beta)]}$$

$$\frac{\partial I_C}{\partial \beta} = S = \frac{(1+\beta)(R_B + R_E)}{R_B + (1+\beta)R_E}$$

Multiply NR & DR by  $\beta$ ,

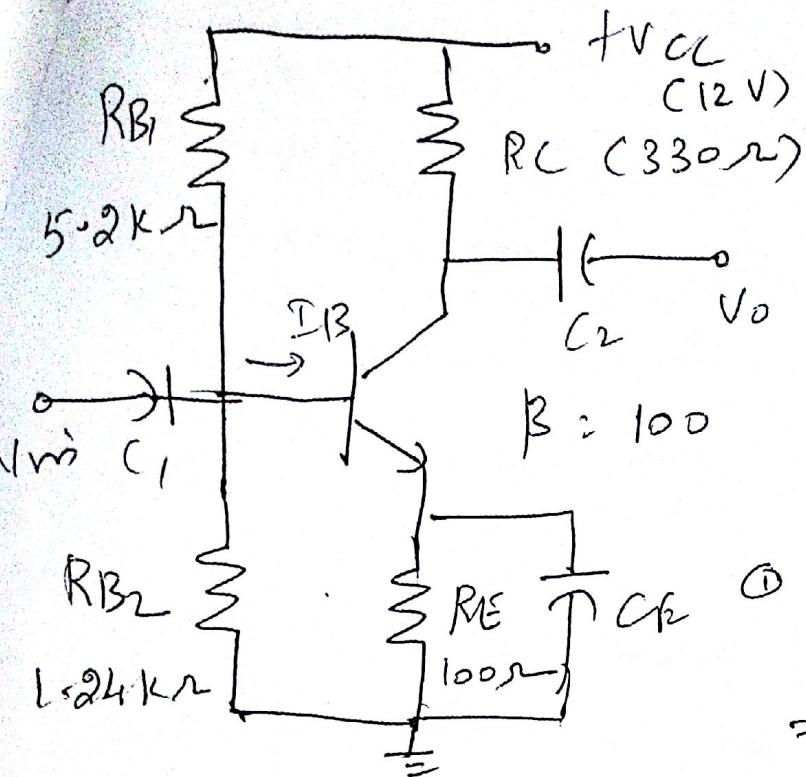
$$\frac{\partial I_C}{\partial \beta} = \frac{\beta (V_{TH} + V' - V_{BE}) \cdot S}{[R_B + R_E(1+\beta)] (1+\beta) \cdot \beta}$$

$$\frac{\partial I_C}{\partial \beta} = \frac{\beta (V_{TH} + V' - V_{BE}) \cdot S}{[R_B + R_E(1+\beta)] (1+\beta) \cdot \beta}$$

$$\frac{\partial I_c}{\partial \beta} = \frac{I_c - S}{\beta(1+\beta)}$$

$$S'' = \frac{I_c - S}{\beta(1+\beta)}$$

problem



Draw the DC load line for the following transistor configuration  
to obtain the Q-point

Solution:

$$\textcircled{1} \quad V_{TH} = \frac{R_{B2} \cdot V_{CC}}{R_{B1} + R_{B2}}$$

$$= \frac{1.24 \text{ k} \times 12}{5.2 \text{ k} + 1.24 \text{ k}} = 2.31 \text{ V}$$

$$\boxed{V_{TH} = 2.31 \text{ V}}$$

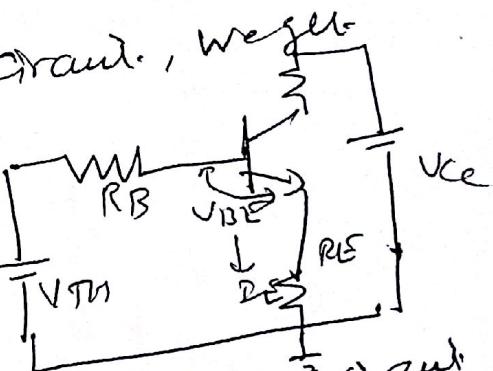
$$\textcircled{2} \quad R_B = R_{B1} \parallel R_{B2}$$

$$= 5.2 \text{ k} \parallel 1.24 \text{ k}$$

$$\boxed{R_B = 1.1 \text{ k}}$$

Applying KVL to the base circuit, we get

$$I_B = \frac{V_{TH} - V_{BE}}{R_B + (1+\beta)R_E} = 145 \mu\text{A}$$



$$\begin{aligned} V_{TH} &= I_B R_B + V_{BE} + I_E R_E \\ &= I_B R_B + V_{BE} + (1+\beta) I_B R_E \end{aligned}$$

$$I_C = \beta I_B = 100 \times 145 \mu\text{A} = 14.5 \text{ mA}$$

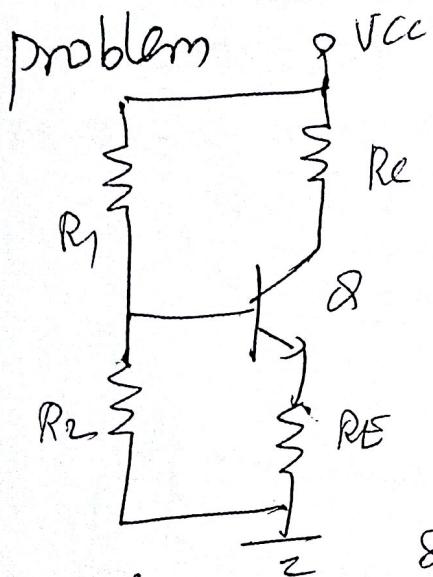
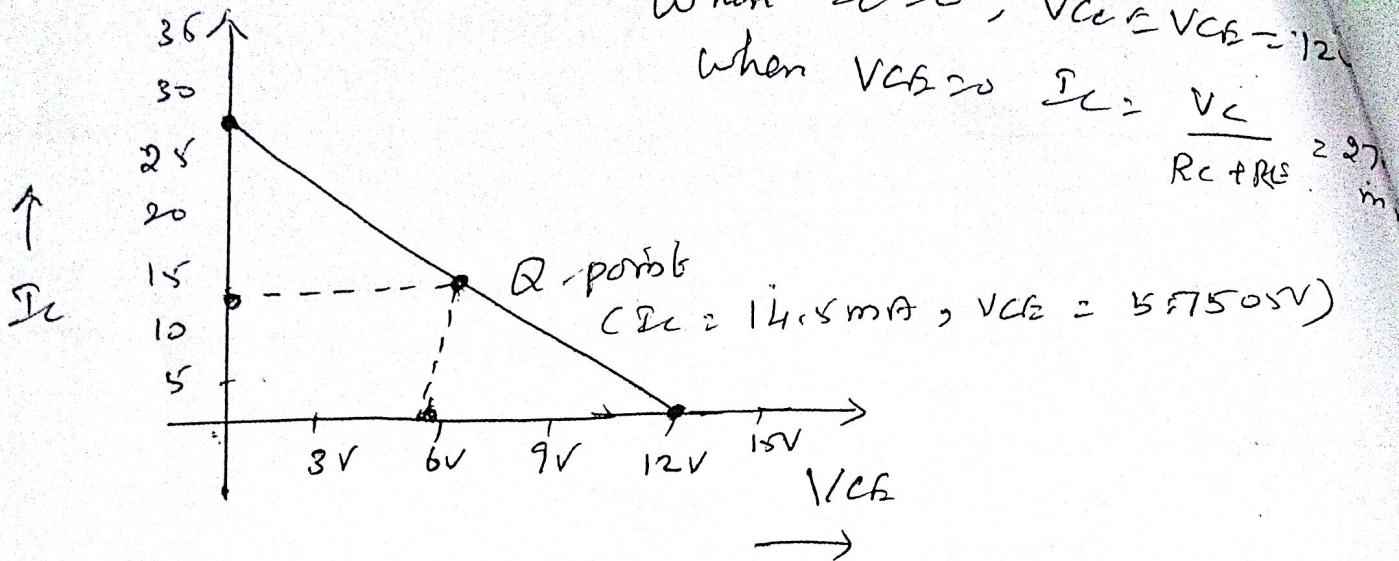
$$\boxed{I_C = 14.5 \text{ mA}}$$

$$V_{CE} = I_C R_C + V_{CE} + I_E R_E$$

$$V_{CE} = V_{CC} - I_C R_C - I_E R_E = V_{CC} - I_C R_C - (1+\beta) I_B R_E$$

$$= 12 - 14.5 \text{ mA} \times 330 - 145 \mu\text{A} \times 100$$

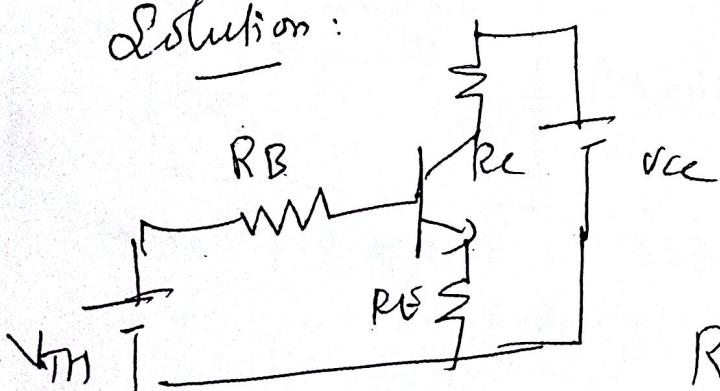
$$\frac{1}{V_{CE} - 4.7505 \text{ V}}$$



For the given circuit diagram  
 $V_{CC} = 20V$ ,  $R_C = 2k\Omega$ ,  $\beta = 50$ ,  
 $V_{BE} = 0.2V$ ,  $R_I = 100k\Omega$ ,  
 $R_E = 100\Omega$ . Calculate  $I_B$ ,  
 $V_{CE}$ ,  $I_C$  and stability factor  $S$ .

$R_2$  is not given, assume  $R_2 = 10k\Omega$

Solution:



$$V_{TM2} = \frac{R_B V_{CC}}{R_B + R_{B2}} = \frac{20 \times 10}{100 + 10} = 1.818V$$

$$V_{TM} = 1.818V$$

$$R_{IB} = R_I || R_2 = 9.09k\Omega$$

$$I_B = \frac{V_{TM} - V_{BE}}{R_B + (1+\beta)R_E} = \frac{1.818 - 0.2}{9.09k\Omega + (1+50)100} = 1.812 \text{ mA}$$

$$I_B = 1.812 \text{ mA}$$

$$I_C = \beta I_B = 5.7 \text{ mA}$$

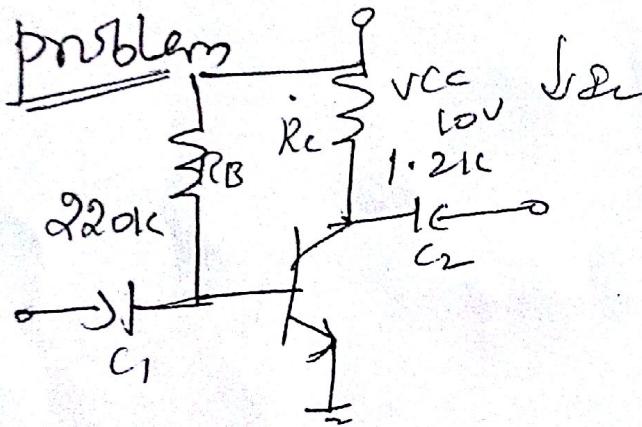
$$V_{CE} = V_{CC} - I_C R_C - (1 + \beta) I_B R_E$$

$$V_{CE} = 8 \text{ V}$$

$$S = \frac{1 + \beta}{1 + \beta \left( \frac{R_E}{R_B + R_E} \right)}$$

$$= \frac{1 + 50}{1 + 50 \left( \frac{100}{100 + 9.09 \times 10^3} \right)}$$

$$\boxed{S = 33}$$



For the given circuit.  
Calculate  $I_B, I_C, V_{CE}, V_B, V_C \& V_{BE}$

Assume  $V_{BE} = 0.7 \text{ V}; \beta = 50$

Solution:

$$I_B = \frac{V_{CC} - V_{BE}}{R_B} = \frac{10 - 0.7}{220 \times 10^3} = 42.27 \mu\text{A}$$

$$I_C = \beta I_B = 50 \times 42.27 \times 10^{-6} = 2.1135 \text{ mA}$$

$$V_{CE} = V_{CC} - I_C R_C = 10 - 2.1135 \times 10^3 \times 1.2 \times 10^3$$

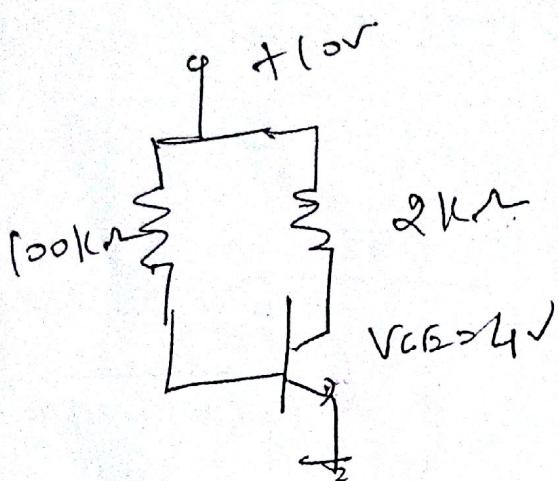
$$V_{CE} = 7.4638 \text{ V}$$

$$V_B = V_{BE} = 0.7 \text{ V}$$

$$V_C = V_{CE} = 7.463 \text{ V}$$

$$V_{BC} = V_B - V_C = 0.7 - 7.4638 = -6.7638$$

Pblm for the given circuit calculate Stability factor.



$$S = 1 + \beta$$

$$\beta = \frac{\Delta I_C}{\Delta I_B}$$

$$V_{CC} = \Delta C R_C + V_{CE}$$

$$\Delta C = \frac{V_{CC} - V_{CE}}{R_C} = 3mA$$

$$V_{CC} = I_B R_B + V_{BE}$$

$$\Delta I_B = \frac{V_{CC} - V_{BE}}{R_B} = 93\mu A$$

$$\beta = \frac{\Delta I_C}{\Delta I_B} = 32.288$$

$$\boxed{S = 1 + \beta = 33.288}$$